

Wherever there's HLTTL... there's Transitron



The Transitron philosophy in integrated circuits has resulted in the concentration of its production capability first on a family of digital monolithic circuits called High Level Transistor Transistor Logic (HLTTL). There is, of course, intention to manufacture linear integrated circuits and perhaps even other families of digital circuits in the near future. However, it is believed that the family of integrated circuits with the greatest appeal to circuit and system designers today and for the systems producer for the next several years is without question HLTTL. Therefore, the past year has been devoted almost entirely to the establishment of good manufacturing capability of such circuits. Transitron's concentration of effort on this family has resulted in an unprecedented number of different circuit functions and gates for the application of logic system designers; a strong improvement in the propagation delay, the radiation resistance and the output characteristic of the circuits; a new master slave flip-flop for single phase application; a willingness to do custom work within the basic HLTTL circuit concept for new functions; a similar willingness to alternate source other manufacturers' HLTTL functions and pin configurations; and finally a low cost set of HLTTL circuits for commercial application. All of this is detailed in the succeeding pages of this brochure. It has been our intent to make evident, by performance, the slogan, "Wherever There's HLTTL ... There's Transitron." The industry response to this philosophy has been gratifying.

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Transitron

Integrated Circuit Operations



CRYSTAL GROWING -

Single crystal Czochralski silicon crystals are grown in furnaces designed and built by Transitron. Dopants used are antimony, arsenic, phosphorous and boron. The crystals are cut, lapped and polished prior to further processing.



MASK MAKING -Integrated circuit photomasks are made in Transitron's photographic laboratory. Both the standard emulsionon-glass type mask and evaporated chromiumon-glass masks are produced. An intermediate master is made from the original art work on a precision reduction camera capable of resolving a 3 micron line width. The master mask is then made from the intermediate mask on a Photorepeater, which has a positional error of less than .5 micron. A solid state counter andshaft encoder control stepping distance. Comparators, accurate to .5 micron in two coordinates are used to inspect the masks. With this equipment, and the processing techniques developed by Transitron, line widths of one micron and registration errors of less than one micron are achieved.

MASK ALIGNMENT -

Mask alignment is performed on equipment designed and built at Transitron. This alignment equipment is a significant advancement over commercially available equipment and has a registration error of less than 0.5 micron.









FURNACES — Diffusion is performed in single zone furnaces. The furnaces for diffusion of P-type and N-type dopants are physically separated in different controlled atmosphere rooms. These furnaces provide temperatures up to 1300°C with a temperature stability of ± 0.5 °C and are solid state module controlled.

MULTIPLE PROBE TESTING — Automatic test equipment is used for testing the dice on the slice prior to scribing and mounting in the package.

DIE MOUNTING — The integrated circuits are packaged using semiautomatic die mounting equipment. One of the unique features is the automatic die edge pickup which eliminates any possible surface damage.



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BONDING — Aluminum leads are ultrasonically bonded to the integrated circuit, also using Transitron designed and fabricated equipment.

TESTING — Each Transitron integrated circuit is tested on automatic, high-speed, multiparameter test systems. These test systems, which were designed and constructed at Transitron, also include a punched paper tape output of test results for data logging and computer analysis of test data.

Transitron HLTTL Integrated Circuits





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GATED 2-PHASE

FLIP-FLOP

TFF 3011F 3012F 3013F 3014F

TFF 3011 3012 3013 3014

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Transitron HLTTL Circuit Listing

NOTE: Package Key as follows:

(a) T = 12 lead, short cap, TO-5 package — For units in this package use type number as listed.

(b) F = 14 lead, .195 x .260 inch flat package — For units in this package use type numbers with F suffix (e.g., TNG3011F).

Tune Number	Deckers	
TNG3011 thru 3014	Раскаде	Circuit Description
TNG3015 thru 3018		Single 6 input Nand/Nor Gate
TNG3041 thru 3044	ET 1	Single 8 input Nand/Nor Gate
TNG3045 thru 2048		Single 8 input Nand/Nor Gate with 10 nsec tpd
TNG3043 (III/0 3046		Single 6 input Nand/Nor Gate with 10 nsec tpd
TNG3051 (III'u 3054		Single 8 Input Nand/Nor Gate, expandable
TNG3115 thru 3114		Dual 2 input Nand/Nor Gate
TNC3141 thru 3144		Dual 4 input Nand/Nor Gate
TNG3141 tirru 3144	F, 1	Dual 4 input Nand/Nor Gate with 10 nsec tpd
TNG3145 thru 3146		Dual 3 input Nand/Nor Gate with 10 nsec tpd
TNG3211 tillu 3214		
TNG3215 thru 3218		Dual 3 input Nand/OR Gate
TNG3241 thru 3244	F, I M	Dual 4 input Nand/OR Gate with 10 nsec tpd
TNG3245 thru 3248		Dual 3 input Nand/OR Gate with 10 nsec tpd
TNG3251 thru 3254	E A	Dual 4 input Nand/OR Gate, expandable
TNG3311 thru 3314	F)	Triple 3 input Nand/Nor Gate
TNG3411 thru 3414	F) /	Quad 2 input Nand/Nor Gate
TNG3511 and 3512	[™] F, T \. (Dual 4 input AND expander Gate
TNG4011 and 4012	F, T /	Dual 4 input OR expander Gate
TNG4211 thru 4214	EF)	Dual Exclusive OR Gate
TNG4251 thru 4254	F	Dual Exclusive OR Gate, expandable
TNG4311 thru 4314	F (Triple 3 input Nand/OR Gate
TNG4315 thru 4318	F	Triple 3 input Nand/OR Gate, expandable
TNG4411 thru 4414	È (Quad 2 input Nand/OR Gate
TNG4415 thru 4418	MF (Quad 2 input Nand/OR Gate, expandable
TNG4511 and 4512	F (Quad 2 input OR expander Gate
TNG4611 thru 4614	F)	Exclusive OR with complement
TNG5121 thru 5124	F) (Single 4 input Line or Clock Driver
TNG5221 thru 5224	F	Dual 2 input Line or Clock Driver
TNG5321 thru 5324	F	Single 4 input Lamp Driver
TNG5421 thru 5424	F) (Dual 2 input Lamp Driver
TFF3011 thru 3014	T,F	Dual 3 input Gated 2 phase flip-flop
TFF3015 thru 3018	T,F	Dual 2 input Gated 2 phase flip-flop
TFF3111 thru 3114	FI	Master Slave Flip-Flop 4 input with Buffer
TFF3115 thru 3118	T,F)	Master Slave Flip-Flop 2 input with Buffer
TFF3121 thru 3124	T,F (Master Slave Flip-Flop 4 input without Buffer
TFF3125 thru 3128	T, F	Master Slave Flip-Flop 2 input without Buffer
TFF3211 thru 3214	F	Charge Storage J-K flip-flop
TFF3251 thru 3254	F (Chg. Storage J-K flip-flop, Expandable for OR
		For Out and Operating Tamparature
		as Indicated by Type Number

Type No.

1 and 2 and 3 and

4 and

Fan Out

15 (40) 15 (40) 7 (24) 7 (24) Temp. Range °C

-55 to +125 0 to + 75 -55 to +125 0 to + 75

Transitron HLTTL Integrated Circuit **Manufacturers'** Type **Cross-reference** and Pin Configuration Guide

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NOTES:

(1) Under "Temperature Range" column, F equal -55°C to +125°C and R equal 0 to +75°C.

② In "Sylvania type" column the * means that Transitron devices have a higher guaranteed fanout than the Sylvania type listed.

③ In ''Pin Configuration'' column where more than one configuration is listed, the standard Transitron configuration is denoted by a line under the letter (e.g., \underline{A})

-Key to the pin configurations are as follows:

A = Transitron

B = Sylvania C = Texas Instruments

D = Phoenix Gate

Circuit Description	F. O .	Temp. Range	Transition Type No.	Sylvania Type No.	Texas instr. Type No.	Pin Configurations Available from Transitron
Single 8 input Nand/Nor Gate	15 15 7	FR	TNG3011F TNG3012F TNG3013F TNG3014F	SG60 *SG62 SG61 *SC62	General type SN5430	<u>B</u> , C, D
Single 8 input Nand/Nor Gate, Expandable	7 15 15 7 7	F R F R	TNG3051F TNG3052F TNG3053F TNG3054F	SG120 *SG122 SG121 *SG123		B
Duai 4 input Nand/Nor Gate	15 15 7 7	F R F R	TNG3111F TNG3112F TNG3113F TNG3114F	SG40 *SG42 SG41 *SG43	General type SN5420	<u>B</u> , C, D
Triple 3 input Nand/Nor Gate	15 15 7 7	F R F R	TNG3311 F TNG3312F TNG3313F TNG3314 F	SG190 SG192 SG191 SG193	General type SN5410	<u>А</u> , В, С
Ouad 2 input Nand/Nor Gate	15 15 7 7	F R F B	TNG3411F TNG3412F TNG3413F TNG3414F	SG140 *SG142 SG141 *SG143	General type SN5400	<u>B</u> , C
Dual 4 And Expander Gate	-	FR	TNG3511F TNG3512F	SG180-181 SG182-183		В
Dual 4 input OR Gate, Expandable	15 15 7 7	F R F R	TNG3251F TNG3252F TNG3253F TNG3254F	SG110 *SG112 SG111 *SG113		В
Exclusive OR Gate with Complement	15 15 7	F R F	TNG4611F TNG4612F TNG4613F TNG4614F	SG90 *SG92 SG91 *SG93		В
Dual Exclusive OR Gates	15 15 7	F	TNG4211F TNG4212F TNG4213F		General type SN5450	<u>A</u> , C
Triple 3 input OR Gate, Expandable	7 15 15 7	F R F	TNG4214F TNG4315F TNG4316F TNG4317F	SG100 *SG102 SG101		В
Ouad 2 input OR Gate, Expandable	7 15 15 7	F R F	TNG44318F TNG4415F TNG4416F TNG4417F	SG103 SG50 *SG52 SG51		В
Dual 4 OR Expander Gate	-	F R	TNG4011F TNG4012F	SG170-171 SG172-173	Generai type SN5460	<u>B</u> , C
Quad 2 input OR Expander Gate	_	F R	TNG4511F TNG4512F	SG150-151 SG152-153		В
Single 2 input Line Driver	40 40 24 24	F R F R	TNG5125F TNG5126F TNG5127F TNG5128F	*SG130 *SG132 *SG131 *SG133		В
Dual 4 input Line Driver	40 40 24 24	F R F B	TNG5211F TNG5212F TNG5213F TNG5214F		General type SN5440	C
Dual 3 input Gated 2 phase flip-flop	15 15 7 7	F R F B	TFF3011F TFF3012F TFF3013F TFF3014F	SF20 *SF22 SF21 *SF23		В
4 input Master Slave flip-flop with Buffer	15 15 7 7	F R F B	TFF3111F TFF3112F TFF3113F TFF3114F			A
2 input Master Slave flip-flop with Buffer	15 15 7 7	FR	TFF3115F TFF3116F TFF3117F TFF3117F			A
4 input Master Slave flip-flop without Buffer	15 15 7 7	FRF	TFF3121F TFF3122F TFF3123F TFF3123F			A
2 input Master Slave flip-flop without Buffer	15 15 7 7	FRFP	TFF3125F TFF3126F TFF3127F TFF3127F			A
Charge Storage J-K flip-flop	15 15 7	FRF	TFF3211F TFF3212F TFF3213F TFF3214F	SF50 *SF52 SF51 *SE53		В
		<u> </u>	17732147	3733		

RATINGS

Transitron

specifications

 $T_A = -55$ to $125^{\circ}C$ Gates and Flip Flops F.O. = 15 and 7

F.O. = 40 and 24

Line Drivers

Lamp Driver $I_{\rm L} = 60 \text{ mA}$

HLTTL

Voltage:	Min.	Тур.	Max.	Temperature and Power	Min.	Тур.	Max.
Supply Voltage Supply Surge 1 sec Supply Operating Input Voltage Output Voltage	4.5	5.0	8.0V 12.0V 6.0V 5.5V 5.5V	Operating Storage Thermal Gradient Junction—Air Thermal Gradient	—55 —65		+125°C +200°C .3°C/mW
				Junction—Case Power Diss. per Gate 50% Duty Cycle, Vec = 5V		15mW	.1°C/mW

ELECTRICAL CHARACTERISTICS

	Values @ Temperature Ambient						
$(\mathbf{V}_{ce} \equiv \mathbf{5V})$	Symbol	-55°C	25°C	+125°C	Units		
$V_{out} "1" _{L} = _{L''_{2}}$ @ V_{in} =	V₀ ''1''	2.8 .45	3.2 .45	3.35 .45	V min. V		
V_{out} "1" Threshold $I_L = I_L$ """ @ $V_{in} =$	Voth "1"	2.5 1.0	2.4 1.2	2.7 .9	V min. V		
V_{out} "O" Threshold $I_L = I_{L^{tr}o}$ " @ $V_{tn} =$	• V _{oth} "O"	.45 [°] 2.0	.45 1.7	.45① 1.4	V max. V		
$ \begin{array}{c} V_{out} & 0 \\ @ V_{tn} = \\ \end{array} $	V ₀ ''0''	.40 2.8	.40 2.8	.45(t) 2.8	V max. V		

GATES AND FLIP FLOPS (at all operating temperatures)

$$\begin{split} &I_{1n^{(*0^*)}}=1.33 \text{ mA max. } @ \ V_{1n}=0 V \textcircled{3} \\ &I_{L^{(*0^*)}}=20 \text{ mA (F.O.}=15) \\ &I_{L^{(*0^*)}}=10 \text{ mA (F.O.}=7) \end{split}$$

Power per Gate "ON" $I_s = 6.0 \text{ mA max.}$ [.9 mA per input nodePower per Gate "OFF" $I_s = 3.0 \text{ mA max.}$ [1.8 mA per input nodeCircuit Bkdn. "OFF" $8V_{min} @ I_s = 5.0 \text{ mA}$ [3.0 mA per input nodeInput Bkdn. 5.5V min. @ $I_{in} = 1.0 \text{ mA}$ [3.0 mA per input nodeOutput Leakage Current = 250 μA max. @ $V_{out} = 5.5V$; $V_{in} = 0V$ Output Short Circuit Current = 45 mA max., 10 mA min.@ $V_{out} = V_{in} = 0V$

$$\begin{split} I_{1n}{}^{\mu_1}{}^{\mu_2}{}^{\mu_3} &= 100 \ \mu A \ \text{max.} @ \ V_{1n} &= 4.5 V \textcircled{O} \\ I_{L}{}^{\mu_2}{}^{\mu_3}{}^{\mu_3} &= 1.5 \ \text{mA} \ (F.O. = 15) \\ I_{L}{}^{\mu_2}{}^{\mu_3}{}^{\mu_3} &= .7 \ \text{mA} \ (F.O. = 7) \end{split}$$

[.9 mA per input node, 5.1 mA per output stage] [1.8 mA per input node, 1.2 mA per output stage] [3.0 mA per input node, 2.0 mA per output stage]

Propagation Delay $t_{pd} = \frac{t_{on} + t_{orr}}{2} = 18$ nsec max. = 10 nsec max. (High Speed Version) $T_A = 25^{\circ}C$ (i)

LINE DRIVERS (at all operating temperatures)

$$\begin{split} I_{1n} & \stackrel{_{(1n)}}{_{(1n)}} = 2.7 \text{ mA max.} @ V_{1n} = 0 \text{V}(3) \\ I_{1n} & \stackrel{_{(2n)}}{_{(1n)}} = 54 \text{ mA (F.O.} = 40) \\ I_{1n} & \stackrel{_{(2n)}}{_{(1n)}} = 32 \text{ mA (F.O.} = 24) \end{split}$$

 Power per Gate "ON" $I_s = 12.0 \text{ mA max.}$ [1.8 mA per Power per Gate "OFF" $I_s = 6.0 \text{ mA max.}$

 Power per Gate "OFF" $I_s = 6.0 \text{ mA max.}$ [3.6 mA per Power per Gate "OFF" $I_s = 6.0 \text{ mA max.}$

 Circuit Bkdn. "OFF" 8V min. @ $I_s = 10.0 \text{ mA}$ [6.0 mA per Power per Gate "OFF" $I_{s} = 1.5 \text{ mA}$

 Input Bkdn. 5.5 V_{m1n} @ $I_{1n-} = 1.5 \text{ mA}$ [6.0 mA per Power per Gate "OFF" $I_{s} = 0.0 \text{ mA}$

 Output Leakage Current = 300 μA max. @ $V_{out} = 5.5V$; $V_{1n} = 0$

$$\begin{split} I_{1n} & \stackrel{}{\overset{}_{}}_{1n} \stackrel{}{\overset{}_{}}_{-1} \stackrel{}{\overset{}_{}}_{-1} = 200 \ \mu A \ \text{max.} @ V_{1n} = 4.5 V \textcircled{)} \\ I_{L^{n_1} \stackrel{}{\overset{}_{}}_{-1} \stackrel{}{\overset{}_{-1}}_{-1} = 4.0 \ \text{mA} \ (F.O. = 40) \\ I_{L^{n_1} \stackrel{}{\overset{}_{-1}}_{-1} = 2.4 \ \text{mA} \ (F.O. = 24) \end{split}$$

[1.8 mA per input node, 10.2 mA per output stage][3.6 mA per input node, 2.4 mA per output stage][6.0 mA per input node, 4.0 mA per output stage]

Output Short Circuit Current = 90 mA max., 20 mA min. @ $V_{out} = V_{tu} = 0V$

Propagation Delay $t_{pd} = \frac{t_{on} + t_{off}}{2} = 18$ nsec max. @ F.O. = 1; C_L = 100 pf; T_A = 25°C[®]

LAMP DRIVERS (at all operating temperatures)

 $I_{1n''0''} = 2.7 \text{ mA max.} @ V_{1n} = 0V \textcircled{3} \\ I_{L''0''} = 60 \text{ mA}$

 $I_{1n^{(r_1)}} = 200 \ \mu A \ max @ V_{1n} = 4.5V()$ $I_{L^{(r_1)}} = .5 \ mA \ into \ output \ terminal$

 Power per Gate "ON" $I_s = 12.0 \text{ mA max.}$ [1.8 mA per Power per Gate "OFF" $I_s = 6.0 \text{ mA max.}$

 Power per Gate "OFF" $I_s = 6.0 \text{ mA max.}$ [3.6 mA per Power per Gate "OFF" $I_s = 10.0 \text{ mA}$

 Circuit Bkdn. "OFF" $8V_{min} @ I_s = 10.0 \text{ mA}$ [6.0 mA per Power per Gate "OFF" $I_{s-1} = 1.5 \text{ mA}$

 Input Bkdn. $5.5V_{min} @ I_{in-} = 1.5 \text{ mA}$ [6.0 mA per Power per Gate "OFF" $I_{s-1} = 1.5 \text{ mA}$

 Output Leakage Current = 300 μA max. $@ V_{out} = 8V; V_{in} = 0V$

[1.8 mA per input node, 10.2 mA per output stage] [3.6 mA per input node, 2.4 mA per output stage] [6.0 mA per input node, 4.0 mA per output stage]

NOTES:

- ① .6V max. for lamp drivers
- ② One unit load
- ③ Other inputs @ 4.5V

- ④ Other inputs ground or open
- ⑤ Dependent on ckt function
- Inused input @ logic "1" = 3.5V

RATINGS

Voltage	Min.	Тур.	Max.	
Supply Voltage Supply Surge 1 sec Supply Operating Input Voltage Output Voltage	4.5	5.0	7.0V 12.0V 6.0V 5.5V 5.5V	

]	Temperature and Power	Min.	Тур.	Max.
1	Operating	0		+ 75°C
Ł	Storage	-65		+200°C
L	Thermal Gradient			.3°C/mW
	Junction-Air			
Ł	Thermal Gradient			.1°C/mW
	Junction-Case			
	Power Diss. per Gate		15mW	
	50% Duty Cycle			
	$V_{cc} = 5.0V$			

ELECTRICAL CHARACTERISTICS

(1) = 5.0 V	Values @ Temperature Ambient						
(Vec _ 5.0V)	Symbol	0°C	25°C	75°C	Units		
$ \begin{array}{c} V_{out} & ``1'' \ I_{L} = I_{L''t''} \\ @ \ V_{in} \end{array} $	V₀ ''1''	3.0 .45	3.1 .45	3.15 .45	V min. V		
V_{out} "1" Threshold $I_L = I_{L^{*'1}}$ "	Voth "1"	2.5	2.4	2.5	V min.		
@ V_{in}		1.1	1.2	1.1	V		
V_{out} "0" Threshold $I_L = I_{L''0}$ "	Voth "0"	.45	.45	.45①	V max.		
@ V_{in}		1.9	1.8	1.7	V		
V_{out} "0" $I_L = I_{L''0}$ "	V₀ "0"	.40	.40	.45①	V max.		
@ V_{1n}		2.8	2.8	2.8	V		

GATES AND FLIP FLOPS (at all operating temperatures)

 $I_{in''0''} = 1.33 \text{ mA max.} @ V_{in} = 0V@3$ $I_{L^{4}0^{1}} = 20 \text{ mA} (F.O. = 15)$ $I_{L^{(1)}} = 10 \text{ mA} (F.O. = 7)$

Power per Gate "ON" Is = 6.0 mA max. (5) Power per Gate "OFF" Is = 3.0 mA max. (5) Circuit Bkdn. "OFF" 7V min. @ $I_s = 5.0 \text{ mA}$ Input Bkdn. 5.5V min. @ $I_{1n} = 1.0 \text{ mA}$ Output Leakage Current = 250 μ A max. @ V_{out} = 5.5V; V_{in} = 0V Output Short Circuit Current = 45 mA max., 10 mA min. @ Vout = Vin = 0V

 $I_{in''i''} = 100 \ \mu A \ max. @ V_{in} = 4.5V @ ④$ $I_{L^{11}} = 1.5 \text{ mA} (F.O. = 15)$ $I_{L^{(1)}} = .7 \text{ mA } (F.O. = 7)$

[.9 mA per input node, 5.1 mA per output stage] [1.8 mA per input node, 1.2 mA per output stage] [3.0 mA per input node, 2.0 mA per output stage]

 $\begin{array}{l} \mbox{Propagation Delay } t_{\rm pd} = \ \frac{t_{\rm on} + t_{\rm off}}{2} = 18 \ \mbox{nsec max.} \\ = 10 \ \mbox{nsec max.} \ \mbox{(High Speed Version)} \end{array} \} \begin{array}{l} \mbox{F.O.} = 1; \ \mbox{C}_{\rm L} = 15 \ \mbox{pf;} \\ \mbox{T}_{\rm A} = 25^{\circ} \mbox{C}^{\oplus} \end{array}$

LINE DRIVERS (at all operating temperatures)

 $I_{tn''0''} = 2.7 \text{ mA max.} @ V_{tn} = 0V(3)$ $I_{L^{(1)}} = 54 \text{ mA} (F.O. = 40)$ $I_{L^{(1)}} = 32 \text{ mA} (F.O. = 24)$

Power per Gate "ON" $I_s = 12.0 \text{ mA max.}$ Power per Gate "OFF" I_s = 6.0 mA max.(5) Circuit Bkdn. "OFF" 7V min. @ I_s = 10.0 mA(3) Input Bkdn. 5.5 Vmin @ Iin- = 1.5 mA(+) Output Leakage Current = 300 µA max. @ Vout = 5.5V; Vin = 0

 $I_{in''i''} = 200 \ \mu A \text{ max.} @ V_{in} = 4.5 V$ $I_{L''1''} = 4.0 \text{ mA} (F.O. = 40)$ $I_{L^{(1)}} = 2.4 \text{ mA} (F.O. = 24)$

[1.8 mA per input node, 10.2 mA per output stage] [3.6 mA per input node, 2.4 mA per output stage] [6.0 mA per input node, 4.0 mA per output stage]

Output Short Circuit Current = 90 mA max., 20 mA min. @ Vout = Vin = 0V

Propagation Delay $t_{pd} = \frac{t_{on} + t_{off}}{2} = 18$ nsec max. @ F.O. = 1; C_L = 100 pf; T_A = 25°C(6)

LAMP DRIVERS (at all operating temperatures)

 $I_{in''0''} = 2.7 \text{ mA max.} @ V_{in} = 0V$ $I_{L^{(1)}0^{(1+)}} = 60 \text{ mA}$ Power per Gate "ON" I_s = 12.0 mA max.(5) Power per Gate "OFF" I_{*} = 6.0 mA max. (5) Circuit Bkdn. "OFF" 7V min. @ I_s = 10.0 mA⁽⁵⁾ Input Bkdn. 5.5Vmin @ Iin- = 1.5 mA Output Leakage Current = 300 µA max. @ Vout = 8V; Vin = 0V

NOTES:

- (1) .6V max. for lamp drivers
- One unit load
- ③ Other inputs @ 4.5V

 $I_{in''1''} = 200 \ \mu A \max @ V_{in} = 4.5 V \oplus$ $I_{L^{(1)}} = .5$ mA into output terminal

[1.8 mA per input node, 10.2 mA per output stage] [3.6 mA per input node, 2.4 mA per output stage] [6.0 mA per input node, 4.0 mA per output stage]

④ Other inputs ground or open

- (5) Dependent on ckt function
- 6 Unused input @ logic "1" = 3.5V

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Transitron HLTTL specifications

 $T_A = 0$ to $75^{\circ}C$ Gates and Flip-Flops F.O. = 15 and 7 **Line Drivers** F.O. = 40 and 24 Lamp Drivers

 $I_{\rm L} = 60 \text{ mA}$

() Transitron

HLTTL Commercial Series Integrated Circuits

High Level Transistor Transistor Logic has already become established as the state-of-the-art for saturated switching in military and industrial applications.

In developing a low-cost version of the premium military series, Transitron has placed HLTTL performance within practical reach for the designer of commercial equipment.

It should be emphasized that the cost reductions involved did not involve the chips themselves, which are actually identical to those used in the premium series. The savings lie primarily in the packaging and in the use of conservative specifications.

All units are packaged in an economical but extremely reliable hermetic, 8-lead TO-5 can, and are assembled by means of automated, high-volume production techniques previously perfected in transistor manufacturing operations.

The use of performance specifications which are well within the design limits of the circuit chips has resulted in high production yields and has reduced the requirement for extensive testing.

With their outstanding combination of good fanout, speed, noise protection and capacitive driving capability, these circuits constitute the most flexible and logically powerful line ever introduced for commercial use.

Type Number	Circuit Description
TNG3031	Single 4 input Nand/Nor Gate
TNG4131	Single 3 input Nand/Nor Gate, expandable
TNG4031	Single 4 input AND Expander Gate
TNG5131	Single 2 input Nand/Nor Gate Expandable for OR function
TNG5031	Dual 2 OR Expander Gates
TNG3131	Dual 2 input Nand/Nor Gate
TNG3231	Dual 2 input Nand/OR Gate
TNG3331	Single 4 input Line Driver
TNG3431	Single 4 input Lamp Driver
TFF3031	Gated 2 phase flip-flop
TFF3131	Master Slave J-K flip-flop, 1 set
TFF3231	Charge Storage J-K flip-flop

Listing of Transitron Commercial Circuits

Transitron Commercial Circuits

RATINGS

Transitron

Commercial

 $T_A = 15$ to $55^{\circ}C$ Gates and Flip-Flops

F.O. = 7 Line Drivers

F.O. = 20 Lamp Driver

 $I_{\rm L} = 50 \text{ mA}$

HLTTL Series

Voltage	Min.	Тур.	Max.	Temperature and Power	Min.	Тур.	Max.
Supply voltage			7.0V	Operating	+15*		+55°C
Supply operating voltage	4.5	5.0	6.0V	Storage			+125°C
Input voltage			5.0V	Power per gate,			
Output voltage			5.5V	50% duty cycle,		15mW	
				$V_{ee} = 5.0V$		1	

ELECTRICAL CHARACTERISTICS

$(V_{ee} = 5.0V.; T_A = 25^{\circ}C)$	Symbol	Value	Units
$ \begin{array}{c} V_{out} \ ``1'' \ l_{L} = l_{L''1''} \\ @ V_{in} \end{array} $	V _o ''1''	2.6 .45	V min. V
V_{out} "1" threshold $I_{\rm L} = I_{\rm L^{-1}}$ " @ $V_{\rm in}$	Voth "1"	2.5 1.0	V min. V
V_{out} "0" threshold $I_L = I_{L^{(r)}o}$ " @ V_{in}	Voth "0"	.50① 2.0	V max. V
V_{vu1} "0" $I_L = I_L$ "" @ V_{1u}	V _o ''0''	.50① 2.8	V max. V

GATES AND FLIP FLOPS

$$\label{eq:linear} \begin{split} l_{1n^{**0}} &:= 1.33 \text{ mA max.} @ V_{1n} = 0 V \textcircled{3} \\ l_{L^{**0}} &:= 10 \text{ mA} \end{split}$$

Power per Gate "ON" $I_s = 6.0 \text{ mA}$ Power per Gate "OFF" $I_s = 3.0 \text{ mA}$ Circuit Bkdn. "OFF" 7V min. @ $I_s = 5.0 \text{ mA}$ Input Bkdn. 5.0V min. @ $I_{1n} = 1.0 \text{ mA}$ Output Leakage 250 μ A max. @ V_{out} = 5.5V $I_{1n''1''} = 200 \ \mu A \ max. @ V_{1n} = 3.0V@()$ $I_{L''1''} = 1.5 \ mA$

[.9 mA per input node, 5.1 mA per output stage] [1.3 mA per input node, 1.2 mA per output stage] [3.0 mA per input node, 2.0 mA per output stage]

Input Bkdn. 5.0V min. @ I_{1n} = 1.0 mA(4) Output Leakage 250 μ A max. @ V_{out} = 5.5V V_{1n} = 0V Output Short Ckt. Current = 45 mA max., 10 mA min. @ V_{out} = V_{1n} = 0V Propagation Delay t_{put} = $\frac{t_{on} + t_{off}}{2}$ = 25 nsec max. F.O. = 1 C_L = 15 pf(4)

LINE DRIVERS

Propagation Delay $t_{pd} = \frac{t_{on} + t_{off}}{2} = 25$ nsec max. F.O. = 1 C_L = 100 pf (6)

LAMP DRIVERS

 $I_{1n^{(i_0)'}} = 2.7 \text{ mA max.} @ V_{1n} = 0V$ $I_{L^{(i_0)'}} = 50 \text{ mA}$

 Power per Gate "ON" $I_s = 12.0 \text{ mA}$ [1.8]

 Power per Gate "OFF" $I_s = 6.0 \text{ mA}$ [3.6]

 Ckt. Bkdn. "OFF" 7V @ $I_s = 10.0 \text{ mA}$ [6.0]

 Input Bkdn. 5.0V @ $I_{1n} = 1.5 \text{ mA}$ [6.0]

 Output Leakage 300 μ A max. @ $V_{out} = 7.0V$, $V_{1n} = 0V$

 $I_{1n}^{(1)} = 400 \ \mu A \text{ max.} @ V_{1n} = 3.0V \oplus I_{L}^{(1)} = .5 \text{ mA into output terminal}$

[1.8 mA per input node, 10.2 mA per output stage] [3.6 mA per input node, 2.4 mA per output stage] [6.0 mA per input node, 4.0 mA per output stage]

NOTES:

① .6V max. for lamp drivers

② One unit load③ Other inputs @ 3.0V

④ Other inputs ground or open
⑤ Dependent on circuit function

(6) Unused inputs @ Logic "1" = 3.5V

Transitron

Quality Assurance and Reliability Transitron's Quality Assurance and Reliability Groups report to a Corporate Director who is responsible directly to the President for all aspects of quality assurance and reliability. Included in these groups are the key functions of incoming inspection, process control and outgoing inspection as well as the support functions such as the standards laboratories, life and environmental test facilities, and equipment calibration and certification. All functions operate according to procedures defined in Transitron's Quality Assurance and Reliability Manual.

Quality Assurance, being fully aware that quality and reliability must be inherent in a finished device, assists engineering in evaluation of new integrated circuit products and then works with and complements the manufacturing line in the production of integrated circuits. This effort begins with the quality assurance participation in generation and approval of both manufacturing procedures and engineering changes thereto, and is implemented by the more than forty control and inspection stations on the Transitron HLTTL production line. These stations include lot acceptance of incoming material, in-process control points, and 100% inspections (particularly visual inspections on metallizations and internal bonds). While all stations generate data for analysis and subsequent product improvement, unprecedented amounts of data are generated at several of the process control stations due to the inherent complexity of the circuits. For example, at one control station a sample of 10 circuits is taken several times a day and over 60 parameters per circuit are recorded and control chart plotted.

Further data pertinent to Transitron's HLTTL integrated circuits is generated by the reliability monitoring of the production line. This program samples production over successive six week periods, subjecting parts of the sample to the following tests consisting of:

1. Operating life at 125°C for 1000 hours; consisting of 500 hours in a ring counter, 500 hours in steady state on-off operation.

- 2. High temperature storage life at 200°C for 1000 hours.
- 3. Environmental tests per MIL-STD-750.

baroup I	Subgroup III
Solderability	Shock
Femperature	Vibration fatigue
Moisture resistance	Vibration variable fr
	Constant acceleration

Subgroup II Terminal Strength

Sul

Subgroup IV Salt Atmosphere equency

ata anticipated fro

To cope with the large volume of data anticipated from the integrated circuit operation, as well as the many other semiconductor operations within the Company, the Reliability Group has developed an extensive set of computer programs. The programs include failure rates and confidence limits, averages, standard deviations, frequency distributions and parameter delta shift analysis.

By using the computer programs to analyze both the process control data and the finished device reliability data, excellent information and direction can be fed back to the engineering and manufacturing groups in a timely fashion. The classic failure analysis — corrective action feedback cycle is greatly enhanced by the sophisticated data analysis techniques of examining parameter change distributions, often more informative than an occasional "end-point" failure.

Thus, Transitron's Quality Assurance and Reliability effort begins at the engineering level, monitors the production line, tests the finished product, and analyzes the total data accumulation to provide direction for maintenance of desired quality and reliability levels as well as for future product improvements.

Future

New packaging concepts and larger circuit functions can be expected to play a major role in our digital integrated circuit business.

As indicated at the beginning of this brochure, HLTTL is only the beginning. Other advanced digital families, memory circuits and linear circuits are certainly in Transitron's future. The success of the present production concentration on HLTTL is expected to be duplicated again and again, in these other areas in coming years.

Transitron electronic corporation

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Wherever there's electronics...there's Transitron

Bulletin TNG-1

Transitron

9/66 TECHNICAL DATA

HLTTL NON-INVERTING GATES

This series af HLTTL Nan-Inverting "AND" and "OR" gates have been added as basic elements af Transitran's planar epitaxial high speed HLTTL family af integrated circuits characterized by very law prapagatian delay and high capacitive driving capability. The circuits were designed primarily far applicatian in systems where simplificatian and higher aperating speeds are af prime impartance since two levels af lagic are replaced by ane.

The unique design af this circuit series pravides far (1) extremely sharp voltage transfer characteristics which result in naise margins in excess af 1.3 valts typically, (2) reductian af supply current during switching and (3) typical prapagatian delay times af 12 nanasecands with 15 pf laad and fanaut af 1. Nan-inverting high level driving capability is pravided by the TNG6522 and TNG6524. Same af the circuits affer the passibility af cantralling the autput transients thraugh the use af an external capacitar between the autput and base af the autput transistar. This is particularly useful in applications where length af intercannections would result in excessive naise caupling.

Expansian of lagic capability is pravided through the use of any of 3 expander gates. Use of these expanders requires interconnection of only one circuit terminal which provides for optimized pin utilization on both the gate and expander.

TYPICAL VOLTAGE TRANSFER CHARACTERISTICS

ELEMENTS

(1) TNG 6222 and 6224	Dual 4 input AND Gate with Transient cantral
(2) TNG 6252 and 6254	Expandable Dual 4 input AND Gate
(3) TNG 6262 and 6264	Expandable Dual 3 input AND Gate with Transient Cantral
(4) TNG 6522 and 6524	Expandable 4 input Driver Gate with Transient Cantral
(5) TNG 7252 and 7254	Expandable Dual 2 + 2 input OR Gate
(6) TNG 7712	8 + 3 input Expander Gates
(7) TNG 7812	4 + 4 + 3 input Expander Gate
(8) TNG 7912	Dual 2 + 3 input Expander Gates

LITHO IN U.S A

TNG 6222 / 6224

TNG 6252 / 6254

TNG 6262 / 6264

314

TNG 6522 / 6524

TNG 7252 / 7254

RATINGS

VOLTAGE	Min	Тур	Max	Temperature and Power	Min	Тур	Max
Supply Valtage Supply Operating Input Voltage Output Valtage	4.5	5.0	7.0 V 6.0 V 5.5 V 5.0 V	Operating Temperature Storage Temperature Thermal Gradient Junctian – Air Thermal Grodient Junction – Cose Power Dissipation per Gote 50% Duty Cycle V _{CC} = 5.0 V	0 - 65	40 m W	+75°C +200°C 0.3°C/mW 0.1°C/mW

ELECTRICAL CHARACTERISTICS

	Values @ Ambient Temperature					
CIRCUIT PARAMETER (V _{CC} = 5.0V)	Symbol	0°C	+ 25°C	+ 75 [°] C	Units	
V _{OUT} ''I'' Threshold, I _L = I _L ''I''	^v отн "I"	3.1	3.1	3.1	Vmin	
@ V _{IN} =		1.90	1.80	1.70	V	
V _{OUT} "O" Threshold, I _L = I _L "O"	^V отн ^{*0"}	0.40	0.40	0.40	V max	
[@] V _{IN} =		1.30	1.20	1.10	V	

GATES (At All Operating Temperatures)

I _{!N} "O" = 1.33 mA max	$I_{\rm IN}$ ('I'' = 100 μ A mox @ $V_{\rm IN}$ = 4.5 V (1) (3)
IL ''O'' = 20 mA (F.O. = 15)	I _L ''I'' = 1.5 mA (F.O. = 15)
I _L ''O'' = 10 mA (F.O. = 7)	'L "Ο" = 0.7 mA (F.O. = 7)

Power Per Gate "ON", I_S = 10.9 mA mox ⁽⁴⁾ [1.4 mA Per Input Node, 9.5 mA Per Output Stoge] Power Per Gote "OFF", I_S = 9.4 mA mox ⁽⁴⁾ [0.9 mA Per Input Node, 8.5 mA Per Output Stoge] Circuit Breokdown "ON", 7.0 V min @ I_S = 15.5 mA mox ⁽⁴⁾ [2.0 mA Per Input Node, 13.5 mA Per Output Stoge] Circuit Breokdown "OFF", 7.0 V min @ I_S = 13.6 mA mox ⁽⁴⁾ [1.6 mA Per Input Node, 12.0 mA Per Output Stage] Input Breokdown, 5.5 V min @ I_{IN} = 1.0 mA ⁽³⁾

Output Short Circuit Current = 50.0 mA mox, 20 mA min @ V_{OUT} = 0 V, V_{IN} = 4.5 V

Propogation Delay $t_{pd} = \frac{t_{on} + t_{off}}{2} = 18 \text{ nsec mox}$ $F.O. = 1, C_L = 15 \text{ pf}$ $T_A = 25^{\circ}\text{C}$ (5)

LINE DRIVERS (At All Operating Temperatures)

Ι _{IN} "O" = 1.33 mA @ V _{IN} = Ο V ^① ②	$I_{\rm IN}$ "I" = 100 μ A mox @ $V_{\rm IN}$ = 4.5 V (1) (3)
IL''O'' = 54.0 mA (F.O. = 40.0)	1L "1" = 4.0 mA (F.O. = 40.0)
۱L ''O'' = 32.0 mA (F.O. = 24.0)	۱۲٬۱٬۱ = 2.4 mA (F.O. = 24.0)

Power Per Gote "ON", I_S = 23.1 mA ⁽⁴⁾ [1.4 mA Per Input Node, 21.7 mA Per Output Stoge] Power Per Gote "OFF", I_S = 21.4 mA ⁽⁴⁾ [0.9 mA Per Input Node, 20.5 mA Per Output Stoge] Circuit Breokdown, "ON", 7.0 V min @ I_S = 35.2 mA ⁽⁴⁾ [2.0 mA Per Input Node, 33.2 mA Per Output Stoge] Circuit Breokdown "OFF", 7.0 V min @ I_S = 32.6 mA ⁽⁴⁾ [1.6 mA Per Input Node, 31 mA Per Output Stoge] Input Breokdown 5.5 V min @ I_{IN} = 1.0 mA ⁽³⁾

Output Short Circuit Current = 100 mA mox, 40.0 mA min @ VOUT = 0V, VIN= 4.5 V

Propagotion Deloy
$$t_{pd} = \frac{t_{on} + t_{off}}{2} = 18.0 \text{ nsec mox } @ F.O. = 1.0, C_L = 100 \text{ pf}, T_A = 25^{\circ}C^{(5)}$$

NOTE5:

- 1 One Unit Load
- 2 Other Inputs @ 4.5 V
- 3 Other Inputs Ground Or Open

(4) Dependent on CKT Function

(5) Unused Inputs @ Lagic "1" = 3.5 V

TURN-ON And TURN-OFF DELAY vs. TEMPERATURE For TNG 6252

APPLICATION

8 TNG 6252 8 Unit Laads per Register Side 1 Propagation Delay

ALTERNATIVES USING ONLY INVERTING GATES

16 TNG 4418	8 Unit Laads per Register Side,	1 Propagation Delay
8 TNG 3114 + 4 TNG 3414	8 Unit Laads per Register Side,	2 Prapagation Delays
2 TNG 3414 + 8 TNG 4214	8 Unit Laads per Register Side,	2 Prapagation Delays
Use af TNG 6252 Simplifies Design	, Reduces Package Caunt and Mai	ntains High Operating Speed.

Transitron

HLTTL HIGH SPEED D TYPE FLIP-FLOP

The TFF3512 and TFF3514 are HLTTL raceless dual rank, high speed "D" type Flip-Flops. The flip-flops complement typically on a 50 megacycle input signal. The high operating speeds which are particularly insensitive to heavy loading have been achieved by dual steering of the second rank flip-flap.

The flip-flop design which utilizes HLTTL technology provides the additionol advontages of (1) moximum input gating ta simplify the required external goting, (2) elimination of redundant inputs ond the necessity to supply the doto complement to form the "set" function, (3) connections for holding o lagic"1" are incorporated into the flip-flop, (4) a built in clock buffer reduces the clock line driving requirements, (5) typicol noise immunity in excess of 1.0 volt ond (6) fonouts in excess of 15 with ather chorocteristics ond logic levels typicol of HLTTL circuitry.

The high speed ond extended goting copobility of these units make them extremely desirable for orithmetic ond generol register opplications.

CIRCUIT DIAGRAM

PIN CONFIGURATION

LITHO IN U.S.A

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TRUTH TABLE:

D	н	Qn	Qn + 1	
0	0	φ	0	Where
1	0	ϕ	1	$\phi = \text{Don}^* t \text{ Care}$
0	1	0	0	n ≖ Bit Time
1	1	0	1	
ϕ	1	1	1	

 $Data; D = D_1 \cdot D_2 \cdot D_3 + D_5 \cdot D_6 \cdot D_7 + D_{13} \cdot D_{14}$

Hald; H = H₁₂

(Subscripts = Package Pin Numbers)

RATINGS

Voltage	Min	Тур	Max	Temperature and Power	Min	Тур	Max
Supply Voltage Supply Operating Input Voltage Output Valtage	4.5	5.0	7.0 V 6.0 V 5.5 V 4.5 V	Operating Temperoture Storoge Temperature Thermol Grodient Junctian — Air Thermal Gradient Junctian — Cose Power Dissipatian, 50% Duty Cycle, V _{CC} =5.0 V	0 - 65	150 m₩	+75°C +200°C 0.3°C/m₩ 0.1°C/m₩

ELECTRICAL CHARACTERISTICS @ VCC= 5.0 V

		Temperature			
	Symbol	0°C	+ 25°C	+ 75 [°] C	Units
INPUT:	<u>}</u>				
Input Laad Current (Data Inputs)	I _{IN} ''O''	1.33	1.33	1.33	mAmox
@ V _{IN} ond Clock		0	0	0	v
Other Inputs (Q High)		+4.5	+4.5	+4.5	V
Input Laad Current (Clock Input)	¹ CIN ^{''1''}	1.0	1.0	1.0	mAmox
@ V _{IN} =	1	+3.5	+3.5	+3.5	v
Other Inputs		Open	Open	Open	
Input Leakoge Current (Doto Inputs)	1 _{IN} "!"	0.1	0.1	0.1	mAmox
@ VIN =		+4.5	+4.5	+4.5	V
Other Inputs: (1)		0	0	0	V
(2) (Q High, Clock Low)		+4.5	+4.5	+4.5	V
Input Leokoge Current (Clock Input)	ICIN''0''	0.25	0.25	0.25	mAmox
@ V =		0	0	0	v
Other Inputs		Open	Open	Open	
Input Breakdown Valtage (Data Inputs)	BV	5.5	5.5	5.5	Vmin
		1.0	1.0	1.0	mAmox
Other Inputs: (1)		0	0	0	v
(2) (Q High, Clack Low)		Open	Open	Open	
ΟυΤΡυΤ		80	80	80	mAmox
Output Short Circuit Current	SC	20	20	20	mAmin
		0	0	0	v
Other Output and Clack Input		0	0	0	v
Losis "O" Output Voltage	V "O"	0.40	0.40	0.40	Vmox
	100	1.30	1.20	1, 10	v
L "O" (E O ~ 15) ~		20	20	20	mA
$(E_1, 0) = (0, 0) = (0, 0)$		10	10	10	mA
Lasia UUI Outant Valtage		3.0	3.0	3.0	Vmin
	10	1.90	1.80	1.70	V
		20	20	20	mA
(E 0 7) -		10	10	10	mA
			20	20	
O'' Power Supply Current	I's "U"	38	38	30	
@ Inputs and Clack		0	0	0	v
Outputs		Upen	Upen	Open	
"I" Power Supply Current	's'''	37	37	3/	mAmox
@ Inputs ond Clock		Open	Open	Open	
Outputs		Open	Upen	Upen	
Breokdawn Voltage	BVS	7.0	7.0	7.0	Vmin
I S =		60	60	60	mA
@ V (Inputs and Clock) =		0	0	0	V
Output s		Open	Open	Open	

SWITCHING CHARACTERISTICS

(At V_{CC} = 5.0 V, T_A = 25°C, F.O. Laad = 7, C_L = 15 pf.)Turn-an Delay, t_dan15 nsec. maxTurn-aff Delay, t_daff25 nsec. maxPreset "0" Time, t_{p0}8 nsec. maxPreset "1" Time, t_{p1}6 nsec. max

APPLICATION -

Register Illustrating the Logic Power of the TFF 3512 and TFF 3514

